a fourth transistor for transferring said first voltage to said global word line according to potential of said node;

a local row decoder for selecting a word line in response to said global word line signal of said global row decoder, wherein said local row decoder comprises:

a fifth transistor for transferring said global word line signal to said word line in response to a second signal;

a sixth transistor for transferring said global word line signal to said word line according to a third signal; and

a seventh transistor for transferring a ground voltage to said word line in response to said second signal.

6. (Canceled)

7. (Currently Amended) The decoder circuit of claim, wherein said first and third transistors are consisted of PMOS transistor, and each of said second and fifth transistors are is consisted of an NMOS transistor.

8. (Canceled)

9. (Currently Amended) The decoder circuit of claim 8, wherein said fifth transistor is consisted of a PMOS transistor, and each of said sixth and seventh transistors are is consisted of an NMOS